

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	171	((diamond) near15 (wafer or substrate)) near15 (strecht\$3 or strain\$3 or tight\$3 or constrict\$3)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_T B
2	BRS	L2	171	((diamond) near15 (wafer or substrate)) near15 (strecht\$3 or strain\$3 or tight\$3 or constrict\$3)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_T B
3	BRS	L3	577	((diamond) near15 (wafer or substrate)) near15 (strecht\$3 or strain\$3 or tight\$3 or constrict\$3 or stress\$3)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_T B
4	BRS	L4	352	((diamond) near3 (film or layer) near15 (wafer or substrate)) near15 (strecht\$3 or strain\$3 or tight\$3 or constrict\$3 or stress\$3)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_T B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	18	4 and (device near layer)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	5	4 and (component near layer)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	5	4 and (chip near layer)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	33	4 and (integrated near circuit)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	50	((diamond) near3 (film or layer) near15 (device or component)) near15 (strecht\$3 or strain\$3 or tight\$3 or constrict\$3 or stress\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	756	((diamond) near3 (film or layer)) near15 (strecht\$3 or strain\$3 or tight\$3 or constrict\$3 or stress\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	29	10 and (device near layer)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	18	10 and (component near layer)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	136	(tensile near strain) near15 (percent)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	10	13 and (device near layer)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	116	(tensile near strain) near5 (percent)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	1	15 and (soi)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	554	(device near layer) near10 (soi)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	6	17 and (diamond near5 thick\$4)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L20	0	19 and (diamond near thick\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L19	19	(component near layer) near10 (soi)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	6537	(silicon near3 layer) near10 (soi)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	97	((silicon near3 layer) near10 (soi)) near15 (strain\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	0	((silicon near3 layer) near10 (soi)) near15 (strain\$3) near10 (percent)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L24	0	((silicon near3 layer) near10 (soi)) near15 (strain\$3) same (diamond near5 thick\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	0	((silicon near3 layer) near10 (soi)) near15 (strain\$3) same (diamond)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
26	BRS	L26	1	((silicon near3 layer) near10 (soi)) near15 (tensile near5 strain\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
27	BRS	L27	9	((silicon near3 layer) near10 (soi or insulator)) near15 (tensile near5 strain\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
28	BRS	L28	0	((diamond) near10 (soi or insulator)) near15 (tensile near5 strain\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
29	BRS	L29	0	((diamond) same (soi or insulator)) near15 (tensile near5 strain\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
30	BRS	L30	0	((diamond) and (soi or insulator)) near15 (tensile near5 strain\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
31	BRS	L31	33	(soi or insulator) near15 (tensile near5 strain\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
32	BRS	L32	1	((silicon near3 film) near10 (soi)) near15 (tensile near5 strain\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
33	BRS	L33	0	((silicon near3 material) near10 (soi)) near15 (tensile near5 strain\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
34	BRS	L34	175	((diamond) near15 (wafer or substrate)) near15 (compress\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
35	BRS	L35	2	((diamond) near15 (wafer or substrate)) near15 (compress\$3) near15 (rough\$4)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
36	BRS	L36	12	((diamond) near15 (wafer or substrate)) near15 (compress\$3) near15 (planar\$4)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
37	BRS	L37	95	1 and (rough\$4 or planar\$4)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
38	BRS	L38	82	1 and (rough\$4 or planar\$4) near15 (surface)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
39	BRS	L39	55	1 and (poly\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20040266055 A1	Methods for the control of flatness and electron mobility of diamond coated silicon and structures formed thereby
2			US 20040263028 A1	Electroactive polymers
3			US 20040232807 A1	Electroactive polymer transducers and actuators
4			US 20020050769 A1	Electroactive polymer electrodes
5			US 6812624 B1	Electroactive polymers
6			US 6781284 B1	Electroactive polymer transducers and actuators
7			US 6583533 B2	Electroactive polymer electrodes
8			US 6545384 B1	Electroactive polymer devices
9			US 6543110 B1	Electroactive polymer fabrication
10			US 6376971 B1	Electroactive polymer electrodes